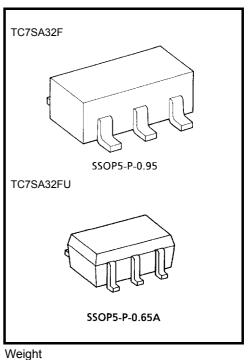
TOSHIBA CMOS Digital Integrated Circuit Silicon Monolithic

TC7SA32F,TC7SA32FU

Low Voltage 2-Input OR Gate with 3.6 V Tolerant Inputs and Outputs

Features

- Low voltage operation : VCC = 1.8~3.6 V
- High speed operation $: t_{pd} = 2.8 \text{ ns} (\text{max}) (V_{CC} = 3.0 \sim 3.6 \text{ V})$
 - $t_{pd} = 3.7 \text{ ns} (\text{max}) (\text{V}_{CC} = 2.3 \sim 2.7 \text{ V})$
 - $t_{pd} = 7.4 \text{ ns} (max) (V_{CC} = 1.8 \text{ V})$
- High Output current $: I_{OH}/I_{OL} = \pm 24 \text{ mA (min)} (V_{CC} = 3.0 \text{ V})$ $: I_{OH}/I_{OL} = \pm 18 \text{ mA (min)} (V_{CC} = 2.3 \text{ V})$ $: I_{OH}/I_{OL} = \pm 6 \text{ mA (min)} (V_{CC} = 1.8 \text{ V})$
- Tolerant inputs.
- Power down protection is provided on output.



Weight SSOP5-P-0.95 : 0.016 g (typ.) SSOP5-P-0.65A : 0.006 g (typ.)

Maximum Ratings (Ta = 25°C)

Characteristics	Symbol	Rating	Unit	
Power supply voltage	V _{CC}	-0.5~4.6	V	
DC input voltage	V _{IN}	-0.5~4.6	V	
DC output voltage	Vour	-0.5~4.6 (Note 1)	V	
De output voltage	Vout	-0.5~V _{CC} + 0.5 (Note 2)	v	
Input diode current	I _{IK}	-50	mA	
Output diode current	IOK	±50 (Note 3)	mA	
DC output current	IOUT	±50	mA	
Power dissipation	PD	200	mW	
DC V _{CC} /ground current	ICC	±100	mA	
Storage temperature range	T _{stg}	-65~150	°C	

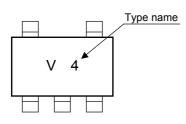
Note 1: $V_{CC} = 0 V$

Note 2: High or low state. $I_{\mbox{OUT}}$ absolute maximum rating be observed.

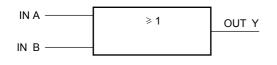
Note 3: $V_{OUT} < GND$, $V_{OUT} > V_{CC}$

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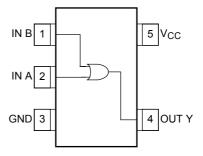
Marking



Logic Diagram



Pin Assignment (top view)



Truth Table

Inp	out	Output
А	В	Y
L	L	L
L	Н	Н
Н	L	Н
Н	Н	Н

Recommended Operating Range

Characteristics	Symbol	Rating	Unit
Power supply voltage	Vee	1.8~3.6	V
Power supply vollage	Vcc	1.2~3.6 (Note 4)	v
Input voltage	V _{IN}	-0.3~3.6	V
Output voltage	V _{OUT}	0~3.6 (Note 5)	V
Output voltage		0~V _{CC} (Note 6)	v
		±24 (Note 7)	
Output current	I _{OH} /I _{OL}	±18 (Note 8)	mA
		±6 (Note 9)	
Operating temperature range	T _{opr}	-40~85	°C
Input rise and fall time	dt/dv	0~10 (Note 10)	ns/V

Note 4: Data retention only

Note 5: $V_{CC} = 0 V$

Note 6: High or low state

Note 7: $V_{CC} = 3.0 \sim 3.6 \text{ V}$

Note 8: $V_{CC} = 2.3 \sim 2.7 \text{ V}$

Note 9: $V_{CC} = 1.8 V$

Note 10: $V_{IN} = 0.8 \sim 2.0 \text{ V}, \text{ V}_{CC} = 3.0 \text{ V}$

Electrical Characteristics

DC Characteristics (Ta = $-40 \sim 85^{\circ}$ C, 2.7 V < V_{CC} \leq 3.6 V)

Characteristics		Symbol	Tor	Test Condition		Min	Мах	Unit	
Charac	clensics	Symbol	168			IVIIII	IVIAX	Onit	
Input voltage	High level	V _{IH}		_	2.7~3.6	2.0	_	v	
input voltage	Low level	V _{IL}		_	2.7~3.6	_	0.8	v	
				I _{OH} = −100 μA	2.7~3.6	V _{CC} - 0.2			
	High level	V _{OH}	V _{IN} = V _{IH}	I _{OH} = -12 mA	2.7	2.2	_	V	
				I _{OH} = -18 mA	3.0	2.4	_		
Output voltage				I _{OH} =24 mA	3.0	2.2	_		
					I _{OL} = 100 μA	2.7~3.6	_	0.2	
	Low level			Max		I _{OL}	I _{OL} = 12 mA	2.7	
	Low level	V _{OL}	VIN – VIL	$V_{IN} = V_{IL}$	I _{OL} = 18 mA	3.0	_	0.4	
				I _{OL} = 24 mA	3.0		0.55		
Input leakage curre	ent	l _{IN}	V _{IN} = 0~3.6 V	V _{IN} = 0~3.6 V		_	±5.0	μA	
Power off leakage	current	IOFF	V _{IN} , V _{OUT} = 0~3.6 V		0		10.0	μA	
O is seen to see the			$V_{IN} = V_{CC}$ or C	$V_{IN} = V_{CC}$ or GND		_	20.0		
Quiescent supply of	Gunefil	Icc	$V_{CC} \leq (V_{IN}, V_{OUT}) \leq 3.6 \text{ V}$		2.7~3.6		±20.0	μA	
Increase in I _{CC} pe	r input	Δlcc	$V_{IH} = V_{CC} - 0.$	6 V	2.7~3.6	_	750		

DC Characteristics (Ta = -40~85°C, 2.3 V \leq V_{CC} \leq 2.7 V)

Characteristics		Symbol	Symbol Test Condition			Min	Мах	Unit														
		Symbol Test Condition		V _{CC} (V)	IVIIII	wax	Unit															
Input voltage	High level	VIH		_	2.3~2.7	1.6		v														
input voltage	Low level	V _{IL}			2.3~2.7	_	0.7	v														
				I _{OH} = -100 μA	2.3~2.7	V _{CC} - 0.2	_															
	High level	V _{OH}	VIN = VIH	VIN = VIH	VIN = VIH	I _{OH} = -6 mA	2.3	2.0	_													
Output voltage			I _{OH} = -12 mA	2.3	1.8		v															
			I _{OH} = -18 mA	2.3	1.7																	
			V _{IN} = V _{IL}	I _{OL} = 100 μA	2.3~2.7		0.2															
	Low level	V _{OL}		$V_{\text{IN}} = V_{\text{IL}}$	$V_{IN} = V_{IL}$	$V_{IN} = V_{IL}$	$V_{IN} = V_{IL}$	$V_{IN} = V_{IL}$	$V_{IN} = V_{IL}$	$V_{IN} = V_{IL}$	$V_{IN} = V_{IL}$	$V_{IN} = V_{IL}$	$V_{IN} = V_{IL}$	$V_{IN} = V_{IL}$	$V_{IN} = V_{IL}$	$V_{IN} = V_{IL}$	$V_{IN} = V_{IL}$	$V_{\text{IN}} = V_{\text{IL}}$	I _{OL} = 12 mA	2.3	_	0.4
			I _{OL} = 18 mA	2.3	_	0.6																
Input leakage current I _{IN} V _{IN} = 0~3		V _{IN} = 0~3.6 V		2.3~2.7	_	±5.0	μA															
Power off leakage	current	IOFF	V _{IN} , V _{OUT} = 0~3.6 V		0		10.0	μA														
Quiescent supply current			$V_{IN} = V_{CC}$ or (V _{IN} = V _{CC} or GND		_	20.0															
		Icc	$V_{CC} \leq (V_{IN}, V_{CC})$	OUT) ≦ 3.6 V	2.3~2.7	_	±20.0	μA														

DC Characteristics (Ta = -40~85°C, 1.8 V \leq V_{CC} < 2.3 V)

Charac	cteristics	Symbol Test Condition			Min	Max	Unit	
onarde		Cymbol			V _{CC} (V)		Max	Onit
Input voltage	High level	VIH			1.8~2.3	$0.7 \times V_{CC}$		V
input voltage	Low level	V _{IL}			1.8~2.3		$0.2 \times V_{CC}$	v
	High level	V _{OH} V _{IN} = V _{IH}	V _{IN} = V _{IH}	I _{OH} = -100 μA	1.8	V _{CC} - 0.2		
Output voltage	-				I _{OH} = -6 mA	1.8	1.4	_
	Low level			I _{OL} = 100 μA	1.8	_	0.2	
	Low level	V _{OL}	$V_{IN} = V_{IL}$	I _{OL} = 6 mA	1.8	_	0.3	
Input leakage curre	ent	l _{IN}	V _{IN} = 0~3.6 V		1.8	_	±5.0	μA
Power off leakage	current	I _{OFF}	V _{IN} , V _{OUT} = 0~3.6 V		0	_	10.0 μA	
Quiescent supply current			$V_{IN} = V_{CC}$ or GND		1.8	_	20.0	
		Icc	$V_{CC} \leq (V_{IN}, V_{OU})$	$V_{CC} \leqq (V_{IN}, V_{OUT}) \leqq 3.6 \ V$		_	±20.0	μA

AC Characteristics (Ta = -40~85°C, input: $t_r = t_f = 2.0 \text{ ns}$, $C_L = 30 \text{ pF}$, $R_L = 500 \Omega$)

Characteristics	Symbol	Test Condition	V _{CC} (V)	Min	Max	Unit
	+	Figure 1, Figure 2	1.8	1.5	7.4	
Propagation delay time			2.5 ± 0.2	1.0	3.7	ns
	^t pHL		$\textbf{3.3}\pm\textbf{0.3}$	0.8	2.8	

For $C_L = 50 \text{ pF}$, add approximately 300 ps to the AC maximum specification.

Capacitive Characteristics (Ta = 25°C)

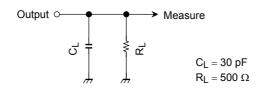
Characteristics	Symbol	mbol Test Condition -			Тур.	Unit
Characteristics	Symbol	Test Condition		V _{CC} (V)	тур.	Unit
Input capacitance	C _{IN}	—		1.8, 2.5, 3.3	6	pF
Power dissipation capacitance	C _{PD}	f _{IN} = 10 MHz	(Note 12)	1.8, 2.5, 3.3	20	pF

Note 12: C_{PD} is defined as the value of the internal equivalent capacitance which is calculated from the operating current consumption without load.

Average operating current can be obtained by the equation.

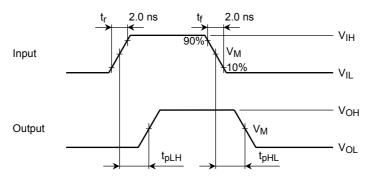
 $I_{CC (opr.)} = C_{PD} \cdot V_{CC} \cdot f_{IN} + I_{CC}$

AC Test Circuit

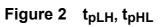




AC Wareform



Symbol	V _{CC}						
Symbol	$3.3\pm0.3~\text{V}$	$2.5\pm0.2\;V$	1.8 V				
VIH	2.7 V	V _{CC}	V _{CC}				
VM	1.5 V	V _{CC} /2	V _{CC} /2				

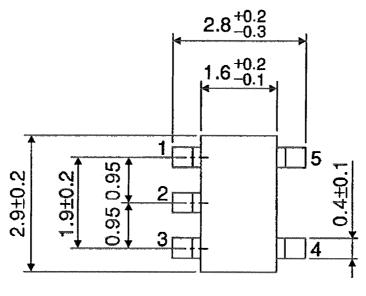


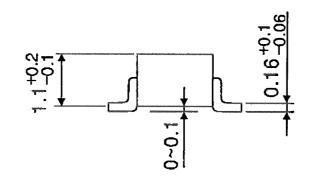
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Package Dimensions

SSOP5-P-0.95

Unit : mm



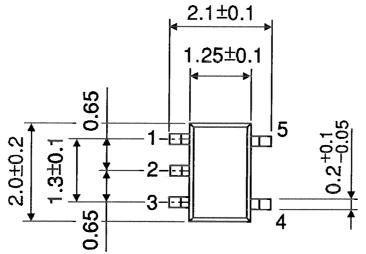


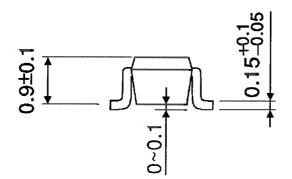
Weight: 0.016 g (typ.)

TOSHIBA

Package Dimensions

Unit : mm





Weight: 0.006 g (typ.)

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